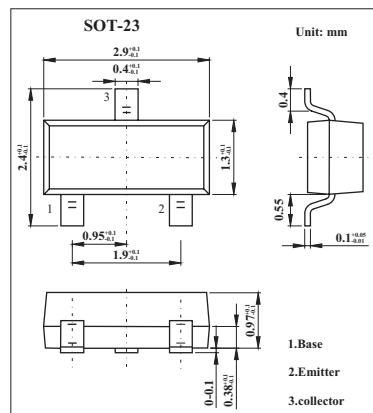


Medium Power Transistor

FMMT555

■ Features

- 150 Volt V_{CEO}
- 1 Amp continuous current



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-160	V
Collector-emitter voltage	V _{CEO}	-150	V
Emitter-base voltage	V _{EBO}	-5	V
Peak collector current	I _{CM}	-2	A
Collector current	I _C	-1	A
Base current	I _B	-200	mA
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100µA	-160			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =-10mA	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100µA	-5			V
Collector cutoff current	I _{CBO}	V _{CB} =-140V			-0.1	µA
		V _{CB} =-140V, Ta = 100°C			-10	µA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V			-0.1	µA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1	V
Base-Emitter Turn-on Voltage *	V _{BE(ON)}	I _C =-100mA, V _{CE} =-10V			-1	V
Static Forward Current Transfer Ratio	h _{FE}	I _C =-10mA, V _{CE} =-10V	50		300	
		I _C =-300mA, V _{CE} =-10V	50			
Transition Frequency	f _T	I _C =-50mA, V _{CE} =-10V, f=100MHz	100			MHz
Output capacitance	C _{obo}	V _{CB} =-10V, f=1MHz			10	pF

* Pulse test: t_p = 300 µs; d ≤ 0.02.

■ Marking

Marking	555
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